

Title (en)  
Semiconductor component and method of manufacture

Title (de)  
Halbleiter-Bauelement und Herstellungsverfahren

Title (fr)  
Composant semi-conducteur et méthode de fabrication

Publication  
**EP 1351286 A3 20050112 (EN)**

Application  
**EP 03007073 A 20030327**

Priority  
US 11478402 A 20020401

Abstract (en)  
[origin: EP1351286A2] A semiconductor component includes a semiconductor substrate (310) having a first conductivity type, a first semiconductor device (320) at least in a first portion of the semiconductor substrate, and a second semiconductor device (330, 340) at least in a second portion of the semiconductor substrate. The first semiconductor device includes a first electrode region (321), a second electrode region (322), a body region (323), and an isolation region (324) in the first portion of the semiconductor substrate. The body region has the first conductivity type, and the first electrode region, the second electrode region, and the isolation region have a second conductivity type. The second electrode region has a different doping concentration than the first electrode region, and the body region is isolated from the second portion of the semiconductor substrate by the isolation region and the first electrode region. <IMAGE>

IPC 1-7  
**H01L 21/761**; H01L 27/088; H01L 21/8234; H01L 29/78; H01L 29/08

IPC 8 full level  
**H01L 21/761** (2006.01); **H01L 21/762** (2006.01); **H01L 29/78** (2006.01); **H01L 29/08** (2006.01)

CPC (source: EP US)  
**H01L 21/761** (2013.01 - EP US); **H01L 21/762** (2013.01 - EP US); **H01L 29/7801** (2013.01 - US); **H01L 29/7816** (2013.01 - EP US); **H01L 29/0653** (2013.01 - EP); **H01L 29/0847** (2013.01 - US); **H01L 29/0886** (2013.01 - EP)

Citation (search report)

- [XY] EP 0682362 A2 19951115 - FUJI ELECTRIC CO LTD [JP]
- [Y] EP 0146181 A2 19850626 - PHILIPS NV [NL]
- [Y] US 2001031533 A1 20011018 - NISHIBE EIJI [JP], et al
- [A] WHISTON S ET AL: "COMPLEMENTARY LDMOS TRANSISTORS FOR A CMOS/BICMOS PROCESS", 12TH. INTERNATIONAL SYMPOSIUM ON POWER SEMICONDUCTOR DEVICES AND IC S.ISPSD 2000. PROCEEDINGS. TOULOUSE, FRANCE, MAY 22 - 25, 2000, INTERNATIONAL SYMPOSIUM ON POWER SEMICONDUCTOR DEVICES & IC'S, NEW YORK, NY : IEEE, US, 22 May 2000 (2000-05-22), pages 51 - 54, XP000987832, ISBN: 0-7803-6269-1
- [A] CORSI M ET AL: "A dual-slot power-interface switch for PCMCIA controllers using a novel bi-directional switching concept, built in a 1 /spl mu/m BiCMOS/DMOS power process", POWER SEMICONDUCTOR DEVICES AND IC'S, 1997. ISPSD '97., 1997 IEEE INTERNATIONAL SYMPOSIUM ON WEIMAR, GERMANY 26-29 MAY 1997, NEW YORK, NY, USA,IEEE, US, 26 May 1997 (1997-05-26), pages 341 - 344, XP010232380, ISBN: 0-7803-3993-2

Designated contracting state (EPC)  
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